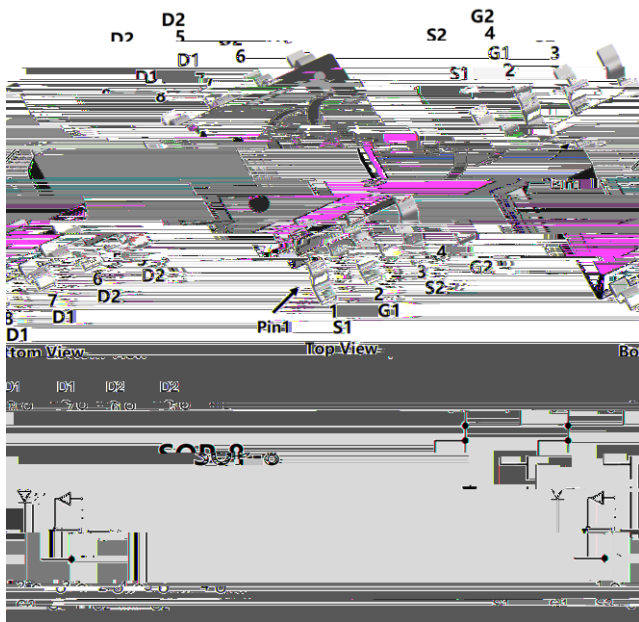




YJS7328B

P-Channel and P-Channel Complementary



Product Summary

- V_{DS}
- I_D
- R_{DS(ON)}(at V_{GS}=-10V)
- R_{DS(ON)}(at V_{GS}=-4.5V)
- 100% EAS Tested

General Description

- Trench Power LV MOSFET
- High density cell design
- High Speed switching
- Moisture Sensitivity
- Epoxy Meets UL 94V-0
- Halogen Free

Applications

- Battery protection
- Load switch
- Power management

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol			
Drain-source Voltage	V _{DS}			
Gate-source Voltage	V _{GS}	±20	V	
Drain Current (Pulse) T _A =25°C	I _D	-10	A	



YJS7328B

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
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Static Parameter



Typical Electrical and Thermal Characteristics Diagrams

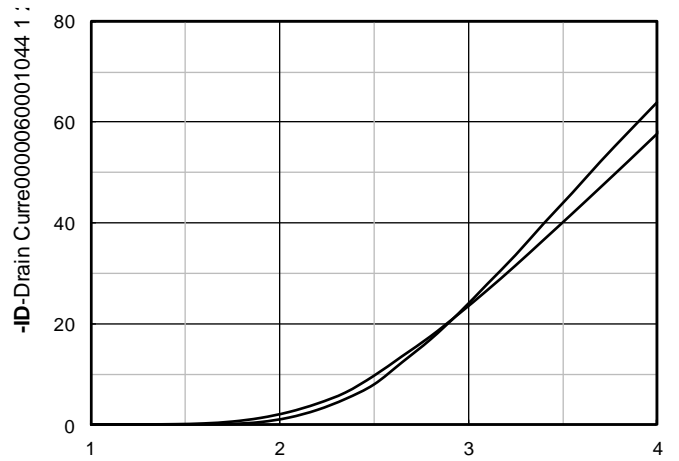
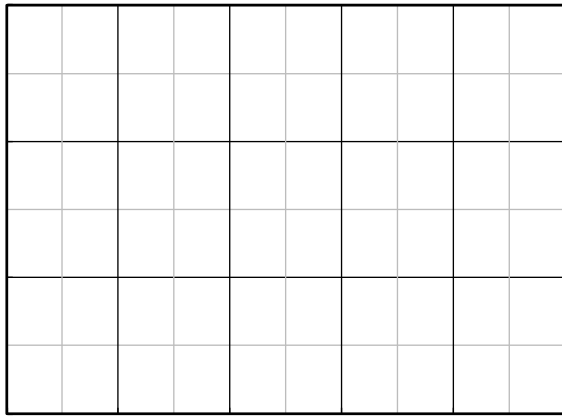


Figure 1. Output Characteristics



YJS7328B

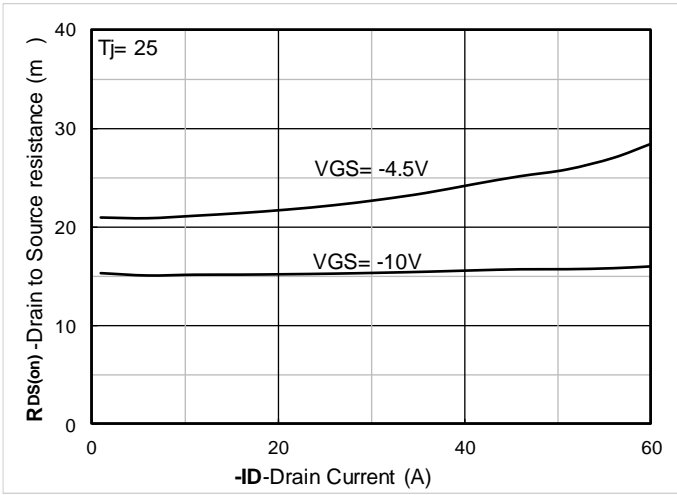


Figure 7. $R_{DS(on)}$ VS Drain Current

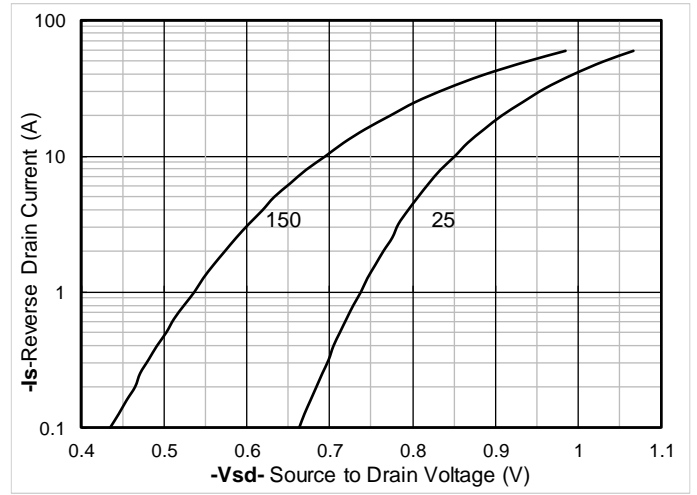


Figure 8. Forward characteristics of reverse diode

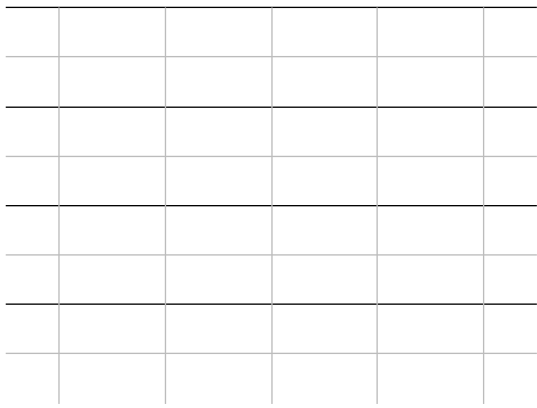


Figure 9. Normalized breakdown voltage

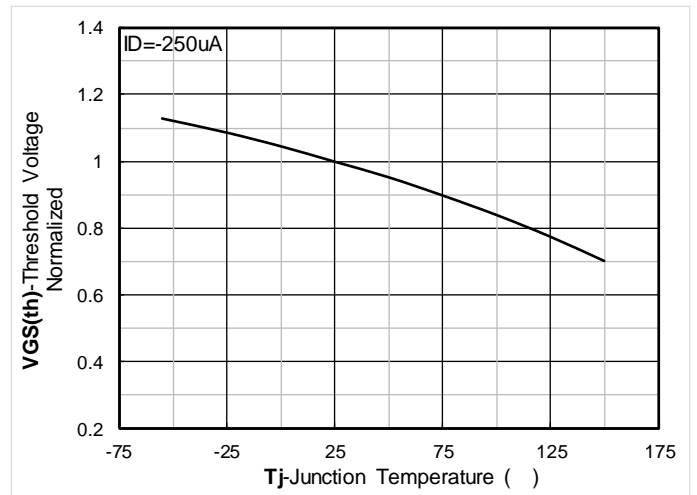
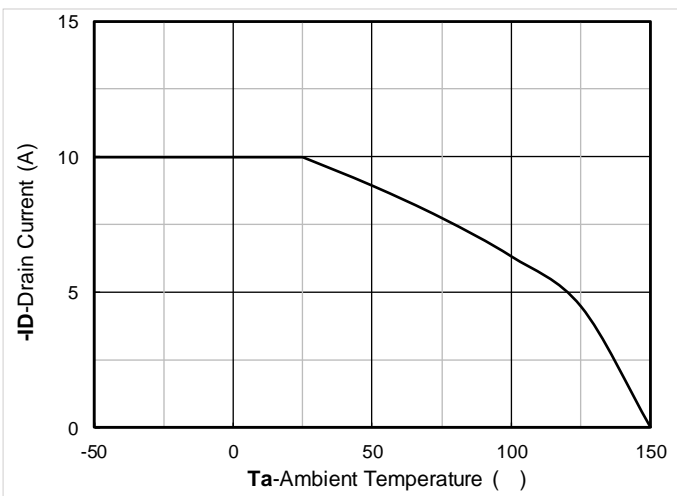
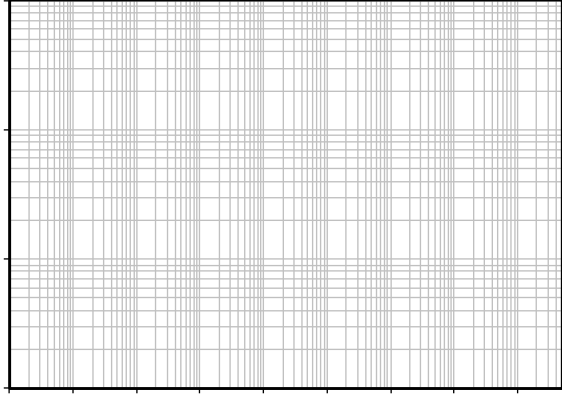


Figure 10. Normalized Threshold voltage







SOP-8 Package information

